

Photo DMOS-FET Relay

Description

The **LT416** is a miniature 1-Form A solid state relay in an 4 pin DIP package that employs optically coupled MOSFET technology to provide 3750V of input to output isolation. The optically coupled input is controlled by a highly efficient GaAlAs infrared LED and MOS FETs on the output side.

Features

- Low driver power requirements (TTL/CMOS Compatible)
- No moving parts
- High reliability
- Arc-Free with no snubbing circuits
- 3750Vrms Input/Output isolation

Applications

- Telecommunications (PC, Electronic notepad)
- Measuring and Testing equipment
- Industrial control
- Security equipments
- High speed inspection machine

Outline Dimensions

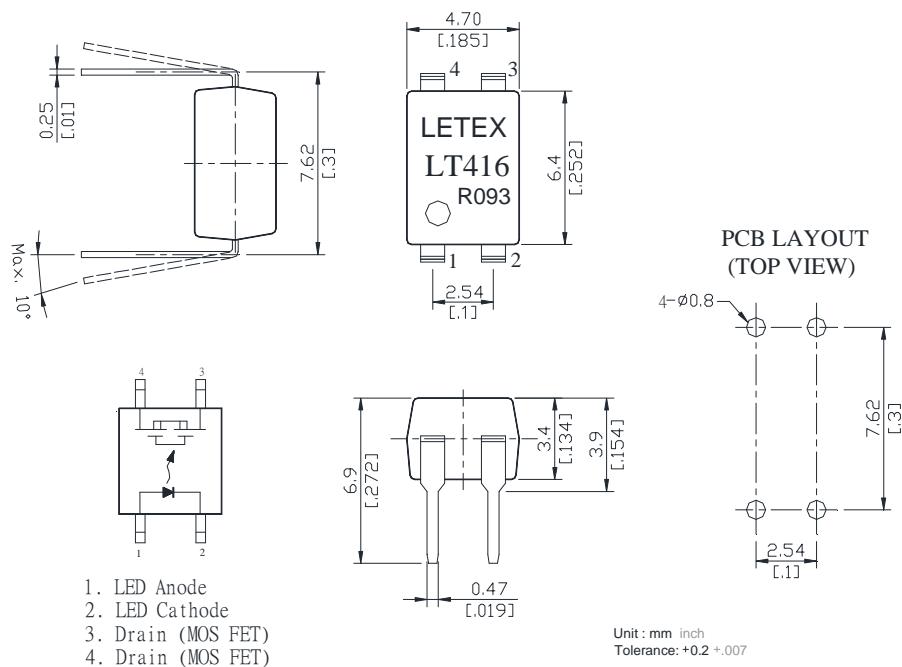


Photo DMOS-FET Relay Specifications**Part Name: LT216**

(Load voltage:20V / Load current: AC:1.7A)

Absolute Maximum Ratings (Ambient Temperature: 25°C)

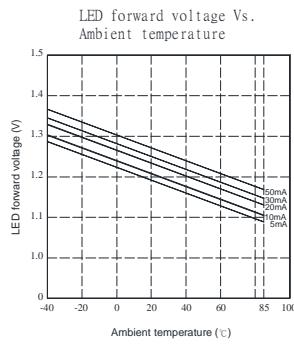
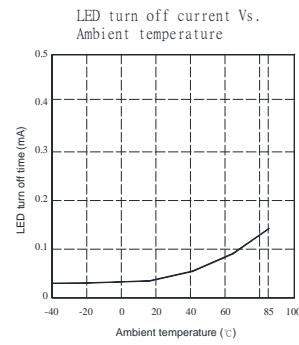
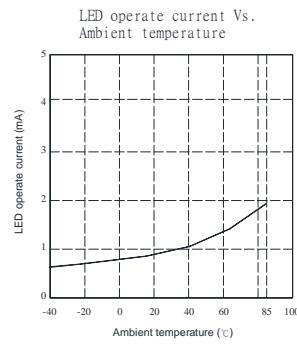
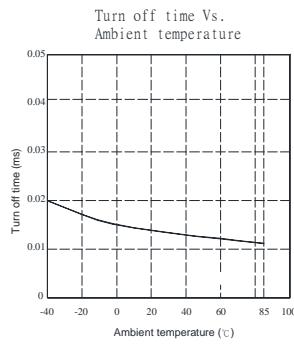
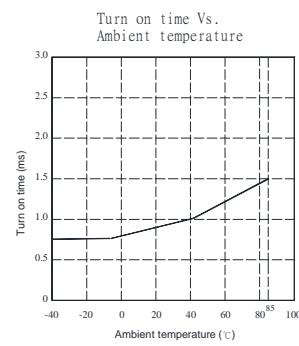
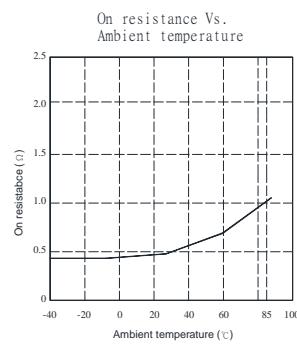
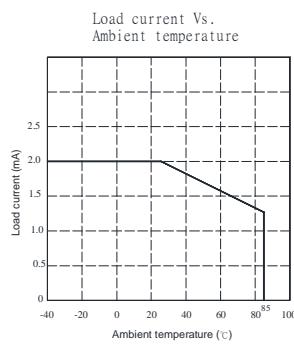
Item	Symbol	Value	Units	Note
Input	Continuous LED Current	I _F	50	mA
	Peak LED Current	I _{FP}	1000	mA
	LED Reverse Voltage	V _R	5	V
	Input Power Dissipation	P _{In}	75	mW
Output	Load Voltage	V _L	20	V(AC peak or DC)
	Load Current	I _L	2	A
	Peak Load Current	I _{Peak}	35	A
	Output Power Dissipation	P _{out}	1.8	W
Total Power Dissipation	P _T	2	W	
I/O Breakdown Voltage	V _{I/O}	3750	Vrms	RH=60%, 1min
Operating Temperature	T _{Op}	-40 to +85	°C	
Storage Temperature	T _{Stg}	-40 to +100	°C	
Pin Soldering Temperature	T _{Sol}	260	°C	10 sec max.

Electrical Specifications (Ambient Temperature: 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input	LED Forward Voltage	V _F		1.2	V	I _F =10mA
	Operation LED Current	I _{F On}		0.5	mA	
	Recovery LED Current	I _{F Off}		0.35	mA	
	Recovery LED Voltage	V _{F Off}	0.5		V	
Output	On-Resistance	R _{on}		0.5	Ω	I _F =5mA, I _L =100mA, Time to flow is within 1 sec.
	Off-State Leakage Current	I _{Leak}		1	μA	V _L =Rating
	Output Capacitance	C _{out}		400	pF	V _L =0, f=1MHz
Transmission	Turn-On Time	T _{on}		1.5	ms	I _F =5mA, I _L =100mA
	Turn-Off Time	T _{off}		0.1	ms	
Coupled	I/O Isolation Resistance	R _{I/O}	10 ⁹		Ω	DC500V
	I/O Capacitance	C _{I/O}		0.8	1.5	pF



Reference Data



Voltage Vs. current characteristics
of output at MOS portion

